What is claimed is:

1. A Eu-doped CsBr-type storage phosphor screen or panel providing ratios of ultraviolet luminescence intensities of at least 10/9 after having been exposed with radiation having a wavelength in the range from 150 to 400 nm , measured at same sites of the screen or panel, once without and once with pretreatment of said storage phosphor screen or panel with short ultraviolet radiation in the range from 150 nm to 300 nm, having an energy of 10 mJ/mm^2.

2. Storage phosphor screen or panel according to claim 1, wherein said ratio is at least 10/7.

3. Storage phosphor screen or panel according to claim 1, wherein said ratio is at least 10/5.

4. Storage phosphor screen or panel according to claim 1, wherein said phosphor is a CsBr:Eu phosphor.

5. Storage phosphor screen or panel according to claim 2, wherein said phosphor is a CsBr:Eu phosphor.

6. Storage phosphor screen or panel according to claim 3, wherein said phosphor is a CsBr:Eu phosphor.

7. Storage phosphor screen or panel according to claim 1, wherein said phosphor is a CsBr:Eu stimulable phosphor, prepared by a method comprising the steps of :
   - mixing said CsBr with between 10^{-3} and 5 mol % of a Europium compound selected from the group consisting of EuX'_2, EuX'_3 and EuOX', X' being a member selected from the group consisting of F, Cl, Br and I,
   - firing said mixture at a temperature above 450 °C

- cooling said mixture and
- recovering the CsBr:Eu phosphor.

8. Storage phosphor screen or panel according to claim 3, wherein said phosphor is a CsBr:Eu stimulable phosphor, prepared by a method comprising the steps of :
- mixing said CsBr with between 10^{-3} and 5 mol % of a Europium compound selected from the group consisting of EuX'_2, EuX'_3 and EuOX', X' being a member selected from the group consisting of F, Cl, Br and I,
- firing said mixture at a temperature above 450 °C
- cooling said mixture and
- recovering the CsBr:Eu phosphor.

9. A binderless storage phosphor screen according to claim 1, containing a CsBr:Eu stimulable phosphor, wherein said screen is prepared by a method comprising the steps of :
- mixing CsBr with between 10^{-3} and 5 mol % of a Europium compound selected from the group consisting of EuX'_2, EuX'_3 and EuOX', X' being a halide selected from the group consisting of F, Cl, Br and I;
- bringing said mixture in condition for vapor deposition and
- depositing said mixture on a substrate by a method selected from the group consisting of physical vapor deposition, thermal vapor deposition,, chemical vapor deposition, electron beam deposition, radio frequency deposition and pulsed laser deposition.

10. A binderless storage phosphor screen according to claim 3, containing a CsBr:Eu stimulable phosphor, wherein said screen is prepared by a method comprising the steps of :
- mixing CsBr with between 10^{-3} and 5 mol % of a Europium compound selected from the group consisting of EuX'_2, EuX'_3 and EuOX', X' being a halide selected from the group consisting of F, Cl, Br and I;

- bringing said mixture in condition for vapor deposition and
- depositing said mixture on a substrate by a method selected from the group consisting of physical vapor deposition, thermal vapor deposition,, chemical vapor deposition, electron beam deposition, radio frequency deposition and pulsed laser deposition.

11. Storage phosphor screen according to claim 1, wherein said phosphor is a CsBr:Eu stimulable phosphor, wherein said screen is prepared by a method comprising the steps of mixing said CsBr with between 10^{-3} and 5 mol % of a Europium compound selected from the group consisting of EuX'_2, EuX'_3 and EuOX', X' being a halide selected from the group consisting of F, Cl, Br and I; firing said mixture at a temperature above 450 °C; cooling said mixture and recovering the CsBr:Eu phosphor; followed by making a lacquer, based on said phosphor, on one or more polymer binders and one or more solvents; coating said lacquer on a substrate and drying a coated layer in order to provide a coated CsBr:Eu phosphor layer.

12. Storage phosphor screen according to claim 3, wherein said phosphor is a CsBr:Eu stimulable phosphor, wherein said screen is prepared by a method comprising the steps of mixing said CsBr with between 10^{-3} and 5 mol % of a Europium compound selected from the group consisting of EuX'_2, EuX'_3 and EuOX', X' being a halide selected from the group consisting of F, Cl, Br and I; firing said mixture at a temperature above 450 °C; cooling said mixture and recovering the CsBr:Eu phosphor; followed by making a lacquer, based on said phosphor, on one or more polymer binders and one or more solvents; coating said lacquer on a substrate and drying a coated layer in order to provide a coated CsBr:Eu phosphor layer.

13. Method of producing a stimulable phosphor screen or panel according to claim 7, characterized in that during or after at least one of the manufacturing steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation

in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

14. Method of producing a stimulable phosphor screen or panel according to claim 8, characterized in that during or after at least one of the manufacturing steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

15. Method of producing a stimulable phosphor screen or panel according to claim 9, characterized in that during or after at least one of the manufacturing steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

16. Method of producing a stimulable phosphor screen or panel according to claim 10, characterized in that during or after at least one of the manufacturing steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

17. Method of producing a stimulable phosphor screen or panel according to claim 11, characterized in that during or after at least one of the manufacturing steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

18. Method of producing a stimulable phosphor screen or panel according to claim 12, characterized in that during or after at least one of the manufacturing steps a radiation exposure treatment is given with

energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

19. Method for producing a binderless storage phosphor screen according to claim 1, said method comprising the steps of :
- providing a CsBr:Eu storage phosphor
- vacuum depositing said phosphor on a substrate characterized in that during said vacuum depositing step said substrate is kept at a temperature T, such that 50 °C ≤ T ≤ 300 °C and that said vacuum deposition proceeds in an Ar-atmosphere with an Ar-pressure of at most 3 Pa, characterized in that during or after at least one of the said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

20. Method for producing a binderless storage phosphor screen according to claim 3, said method comprising the steps of :
- providing a CsBr:Eu storage phosphor
- vacuum depositing said phosphor on a substrate characterized in that during said vacuum depositing step said substrate is kept at a temperature T, such that 50 °C ≤ T ≤ 300 °C and that said vacuum deposition proceeds in an Ar-atmosphere with an Ar-pressure of at most 3 Pa, characterized in that during or after at least one of the said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

21. Method for producing a binderless storage phosphor screen according to claim 1, said method comprising the steps of :
- providing a CsBr:Eu storage phosphor
- vacuum depositing said phosphor on a substrate characterized in that during said vacuum depositing step said substrate is kept at a temperature T, such that 50 °C ≤ T ≤ 300 °C and that said vacuum

deposition proceeds in an Ar-atmosphere with an Ar-pressure of at most 3 Pa, characterized in that during or after at least one of the said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

22. Method for producing a binderless storage phosphor screen according to claim 3, said method comprising the steps of :
- providing a CsBr:Eu storage phosphor
- vacuum depositing said phosphor on a substrate characterized in that during said vacuum depositing step said substrate is kept at a temperature T, such that 50 °C ≤ T ≤ 300 °C and that said vacuum deposition proceeds in an Ar-atmosphere with an Ar-pressure of at most 3 Pa, characterized in that during or after at least one of the said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

23. Method for producing a binderless storage phosphor screen according to claim 1, said method comprising the steps of :
- combining phosphor precursors for a CsBr:Eu storage phosphor,
- vacuum depositing said combination of phosphor precursors on a substrate characterized in that during said vacuum depositing step said substrate is kept at a temperature T, such that 50 °C ≤ T ≤ 300 °C and said vacuum deposition proceeds ion an Ar-atmosphere with an Ar-pressure of at most 3 Pa, characterized in that during or after at least one of the said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

24. Method for producing a binderless storage phosphor screen according to claim 3, said method comprising the steps of :
- combining phosphor precursors for a CsBr:Eu storage phosphor,

- vacuum depositing said combination of phosphor precursors on a substrate characterized in that during said vacuum depositing step said substrate is kept at a temperature T, such that 50 °C ≤ T ≤ 300 °C and said vacuum deposition proceeds ion an Ar-atmosphere with an Ar-pressure of at most 3 Pa, characterized in that during or after at least one of the said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

25. Method for producing a binderless storage phosphor screen according to claim 1, said method comprising the steps of :
- combining phosphor precursors for a CsBr:Eu storage phosphor,
- vacuum depositing said combination of phosphor precursors on a substrate characterized in that during said vacuum depositing step said substrate is kept at a temperature T, such that 50 °C ≤ T ≤ 300 °C and said vacuum deposition proceeds ion an Ar-atmosphere with an Ar-pressure of at most 3 Pa, characterized in that during or after at least one of the said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

26. Method for producing a binderless CsBr:Eu phosphor screen, according to claim 3, said method comprising the steps of :
- mixing or combining CsBr with between 10^{-3} mol % and 5 mol % of a europium compound,
- vapor depositing that mixture onto a substrate, forming a binderless phosphor screen,
- cooling said phosphor screen to room temperature,
- bringing said phosphor screen to a temperature between 80 and 220 °C and
- maintaining it at that temperature for between 10 minutes and 15 hours, characterized in that during or after at least one of the

said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

27. Method for producing a CsBr:Eu stimulable phosphor screen according to claim 1, wherein said screen is prepared by the method comprising the steps of mixing said CsBr with between 10^{-3} and 5 mol % of a Europium compound selected from the group consisting of EuX'_2, EuX'_3 and EuOX', X' being a halide selected from the group consisting of F, Cl, Br and I; firing said mixture at a temperature above 450 °C; cooling said mixture and recovering the CsBr:Eu phosphor; followed by making a lacquer, based on said phosphor, on one or more polymer binders and one or more solvents; coating said lacquer on a substrate and drying a coated layer in order to provide a coated CsBr:Eu phosphor layer, characterized in that during or after at least one of the said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

28. Method for producing a CsBr:Eu stimulable phosphor screen according to claim 3, wherein said screen is prepared by the method comprising the steps of mixing said CsBr with between 10^{-3} and 5 mol % of a Europium compound selected from the group consisting of EuX'_2, EuX'_3 and EuOX', X' being a halide selected from the group consisting of F, Cl, Br and I; firing said mixture at a temperature above 450 °C; cooling said mixture and recovering the CsBr:Eu phosphor; followed by making a lacquer, based on said phosphor, on one or more polymer binders and one or more solvents; coating said lacquer on a substrate and drying a coated layer in order to provide a coated CsBr:Eu phosphor layer, characterized in that during or after at least one of the said steps a radiation exposure treatment is given with energy from radiation sources emitting short ultraviolet

radiation in the range from 150 nm to 300 nm with an energy of at least 10 mJ/mm^2.

29. Method of producing a stimulable phosphor screen or panel according to claim 1, said screen or panel having homogeneous speed distribution over its surface by radiation exposure treatment with energy from a radiation source emitting short ultraviolet radiation in the range from 150 nm to 300 nm to the said storage phosphor plate or panel originally having inhomogeneous speed distribution over its panel surface, by the step of compensating deviations from speed homogeneity point by point by scanning the panel with said radiation source by the step of emitting variable energy amounts in order to compensate for the said deviations.

30. Method of producing a stimulable phosphor screen or panel according to claim 3, said screen or panel having homogeneous speed distribution over its surface by radiation exposure treatment with energy from a radiation source emitting short ultraviolet radiation in the range from 150 nm to 300 nm to the said storage phosphor plate or panel originally having inhomogeneous speed distribution over its panel surface, by the step of compensating deviations from speed homogeneity point by point by scanning the panel with said radiation source by the step of emitting variable energy amounts in order to compensate for the said deviations.

31. Method of producing a stimulable phosphor screen or panel according to claim 1, wherein said screen or panel has a homogeneous speed distribution over its surface by radiation exposure treatment with energy from a radiation source emitting short ultraviolet radiation in the range from 150 nm to 300 nm to the said storage phosphor plate or panel, originally having inhomogeneous speed distribution over its panel surface by the step of compensating deviations from speed homogeneity by integrally irradiating the screen or panel, after covering it partially with one or more filters having

differing densities, thus partially absorbing radiation source emitting short ultraviolet radiation in the range from 150 nm to 300 nm at differing parts.

32. Method of producing a stimulable phosphor screen or panel according to claim 3, wherein said screen or panel has a homogeneous speed distribution over its surface by radiation exposure treatment with energy from a radiation source emitting short ultraviolet radiation in the range from 150 nm to 300 nm to the said storage phosphor plate or panel, originally having inhomogeneous speed distribution over its panel surface by the step of compensating deviations from speed homogeneity by integrally irradiating the screen or panel, after covering it partially with one or more filters having differing densities, thus partially absorbing radiation source emitting short ultraviolet radiation in the range from 150 nm to 300 nm at differing parts.

33. Method according to claim 13, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

34. Method according to claim 14, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

35. Method according to claim 15, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated

- frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

36. Method according to claim 16, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

37. Method according to claim 17, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

38. Method according to claim 18, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

39. Method according to claim 19, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

40. Method according to claim 20, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254

nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

41. Method according to claim 21, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

42. Method according to claim 22, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

43. Method according to claim 23, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

44. Method according to claim 24, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

45. Method according to claim 25, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

46. Method according to claim 26, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

47. Method according to claim 27, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

48. Method according to claim 28, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

49. Method according to claim 29, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

50. Method according to claim 30, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

51. Method according to claim 31, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

52. Method according to claim 32, wherein said radiation source is selected from the group consisting of a mercury vapor lamp at 254 nm, a deuterium lamp, a xenon lamp, a krypton lamp, a quadruplicated - frequency enhanced - Nd:YAg, Nd:YFL, a Nd:YVO or an Alexandrite laser, a dye laser, an excimer laser and a frequency-doubled or quadruplicated diode laser.

53. Method according to claim 33, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

54. Method according to claim 35, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

55. Method according to claim 37, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

56. Method according to claim 39, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

57. Method according to claim 41, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

58. Method according to claim 43, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

59. Method according to claim 45, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

60. Method according to claim 47, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

61. Method according to claim 49, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

62. Method according to claim 51, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

63. Method according to claim 33, wherein said radiation source is selected from the group of gas excimer lasers consisting of F_2, ArF, KrF, XeBr and XeCl.

64. Method of providing a storage phosphor panel according to claim 1, with an identification mark or inscription by means of laser,

mercury vapor lamp or a mask, wherein marking proceeds with a laser having a wavelength in the range from 150 nm to 300 nm.

65. Method of providing a storage phosphor panel according to claim 3, with an identification mark or inscription by means of laser, mercury vapor lamp or a mask, wherein marking proceeds with a laser having a wavelength in the range from 150 nm to 300 nm.

66. Method of providing a storage phosphor panel according to claim 4, with an identification mark or inscription by means of laser, mercury vapor lamp or a mask, wherein marking proceeds with a laser having a wavelength in the range from 150 nm to 300 nm.

67. Method of providing a storage phosphor panel according to claim 6, with an identification mark or inscription by means of laser, mercury vapor lamp or a mask, wherein marking proceeds with a laser having a wavelength in the range from 150 nm to 300 nm.

68. Method according to claim 64, wherein said identification mark or inscription is a readable text or a machine readable code.

69. Method according to claim 65, wherein said identification mark or inscription is a readable text or a machine readable code.

70. Method according to claim 66, wherein said identification mark or inscription is a readable text or a machine readable code.

71. Method according to claim 67, wherein said identification mark or inscription is a readable text or a machine readable code.

72. Method according to claim 68, wherein said identification mark or inscription is a bar code.

73. Method according to claim 69, wherein said identification mark or inscription is a bar code.

74. Method according to claim 70, wherein said identification mark or inscription is a bar code.

75. Method according to claim 71, wherein said identification mark or inscription is a bar code.